

# 74AUP1G00

## Low-power 2-input NAND gate

Rev. 02 — 29 June 2006

Product data sheet

## 1. General description

The 74AUP1G00 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP1G00 provides the single 2-input NAND function.

## 2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM JESD22-A114-C Class 3A. Exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101-C exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu\text{A}$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot  $< 10\%$  of  $V_{CC}$
- $I_{OFF}$  circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

**PHILIPS**

### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP1G00GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G00GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74AUP1G00GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

### 4. Marking

Table 2. Marking

Type number	Marking code
74AUP1G00GW	pA
74AUP1G00GM	pA
74AUP1G00GF	pA

### 5. Functional diagram

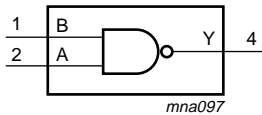


Fig 1. Logic symbol



Fig 2. IEC logic symbol

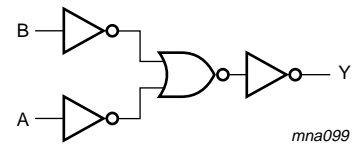


Fig 3. Logic diagram

### 6. Pinning information

#### 6.1 Pinning

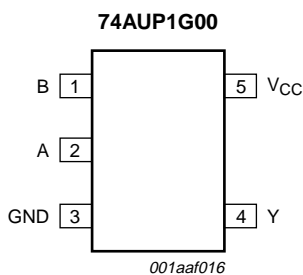


Fig 4. Pin configuration SOT353-1 (TSSOP5)

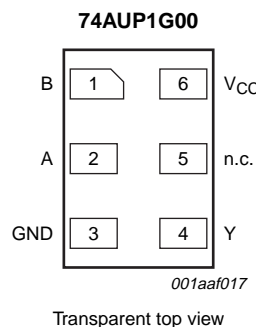


Fig 5. Pin configuration SOT886 (XSON6)

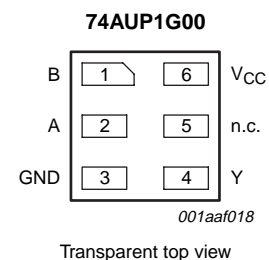


Fig 6. Pin configuration SOT891 (XSON6)

## 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5	XSON6	
B	1	1	data input B
A	2	2	data input A
GND	3	3	ground (0 V)
Y	4	4	data output Y
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

## 7. Functional description

Table 4. Function table<sup>[1]</sup>

Input		Output	
A	B	Y	
L	L	H	
L	H	H	
H	L	H	
H	H	L	

- [1] H = HIGH voltage level;  
L = LOW voltage level.

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-	-50	mA
V <sub>I</sub>	input voltage		[1] -0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> > V <sub>CC</sub> or V <sub>O</sub> < 0 V	-	±50	mA
V <sub>O</sub>	output voltage	Active mode	[1] -0.5	V <sub>CC</sub> + 0.5	V
		Power-down mode	[1] -0.5	+4.6	V
I <sub>O</sub>	output current	V <sub>O</sub> = 0 V to V <sub>CC</sub>	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-	-50	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	[2] -	250	mW

- [1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

- [2] For TSSOP5 packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K.  
For XSON6 packages: above 45 °C the value of P<sub>tot</sub> derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0.8	3.6	V
$V_I$	input voltage		0	3.6	V
$V_O$	output voltage	Active mode	0	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b><math>T_{amb} = 25</math> °C</b>						
$V_{IH}$	HIGH-state input voltage	$V_{CC} = 0.8$ V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9$ V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0$ V to 3.6 V	2.0	-	-	V
$V_{IL}$	LOW-state input voltage	$V_{CC} = 0.8$ V	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9$ V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0$ V to 3.6 V	-	-	0.9	V
$V_{OH}$	HIGH-state output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = -20$ $\mu$ A; $V_{CC} = 0.8$ V to 3.6 V	$V_{CC} - 0.1$	-	-	V
		$I_O = -1.1$ mA; $V_{CC} = 1.1$ V	$0.75 \times V_{CC}$	-	-	V
		$I_O = -1.7$ mA; $V_{CC} = 1.4$ V	1.11	-	-	V
		$I_O = -1.9$ mA; $V_{CC} = 1.65$ V	1.32	-	-	V
		$I_O = -2.3$ mA; $V_{CC} = 2.3$ V	2.05	-	-	V
		$I_O = -3.1$ mA; $V_{CC} = 2.3$ V	1.9	-	-	V
		$I_O = -2.7$ mA; $V_{CC} = 3.0$ V	2.72	-	-	V
		$I_O = -4.0$ mA; $V_{CC} = 3.0$ V	2.6	-	-	V
$V_{OL}$	LOW-state output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = 20$ $\mu$ A; $V_{CC} = 0.8$ V to 3.6 V	-	-	0.1	V
		$I_O = 1.1$ mA; $V_{CC} = 1.1$ V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7$ mA; $V_{CC} = 1.4$ V	-	-	0.31	V
		$I_O = 1.9$ mA; $V_{CC} = 1.65$ V	-	-	0.31	V
		$I_O = 2.3$ mA; $V_{CC} = 2.3$ V	-	-	0.31	V
		$I_O = 3.1$ mA; $V_{CC} = 2.3$ V	-	-	0.44	V
		$I_O = 2.7$ mA; $V_{CC} = 3.0$ V	-	-	0.31	V
		$I_O = 4.0$ mA; $V_{CC} = 3.0$ V	-	-	0.44	V

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_I$	input leakage current	$V_I = \text{GND to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	$\pm 0.1$	$\mu\text{A}$
$I_{\text{OFF}}$	power-off leakage current	$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	$\pm 0.2$	$\mu\text{A}$
$\Delta I_{\text{OFF}}$	additional power-off leakage current	$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	$\pm 0.2$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = \text{GND or } V_{CC}; I_O = 0 \text{ A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	[1]	-	40	$\mu\text{A}$
$C_I$	input capacitance	$V_{CC} = 0 \text{ V to } 3.6 \text{ V}; V_I = \text{GND or } V_{CC}$	-	0.8	-	pF
$C_O$	output capacitance	$V_O = \text{GND}; V_{CC} = 0 \text{ V}$	-	1.7	-	pF

 $T_{\text{amb}} = -40 \text{ }^\circ\text{C to } +85 \text{ }^\circ\text{C}$ 

$V_{IH}$	HIGH-state input voltage	$V_{CC} = 0.8 \text{ V}$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
$V_{IL}$	LOW-state input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
$V_{OH}$	HIGH-state output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O = -20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	$V_{CC} - 0.1$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_O = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_O = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
$V_{OL}$	LOW-state output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O = 20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
$I_I$	input leakage current	$V_I = \text{GND to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	$\pm 0.5$	$\mu\text{A}$
		$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	$\pm 0.5$	$\mu\text{A}$
		$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	$\pm 0.6$	$\mu\text{A}$

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{CC}$	supply current	$V_I = \text{GND or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1]	-	50	$\mu\text{A}$
<b><math>T_{\text{amb}} = -40 \text{ }^\circ\text{C to } +125 \text{ }^\circ\text{C}</math></b>						
$V_{IH}$	HIGH-state input voltage	$V_{CC} = 0.8 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
$V_{IL}$	LOW-state input voltage	$V_{CC} = 0.8 \text{ V}$	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V}$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
$V_{OH}$	HIGH-state output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O = -20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	$V_{CC} - 0.11$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_O = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_O = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_O = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
$V_{OL}$	LOW-state output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		$I_O = 20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
$I_I$	input leakage current	$V_I = \text{GND to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
		$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$I_{OFF}$	power-off leakage current	$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$\Delta I_{OFF}$	additional power-off leakage current	$V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	$\pm 0.75$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = \text{GND or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1]	-	75	$\mu\text{A}$

[1] One input at  $V_{CC} - 0.6 \text{ V}$ , other input at  $V_{CC}$  or GND.

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}</math>; <math>C_L = 5\text{ pF}</math></b>						
$t_{PHL}$ , $t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	17.5	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	2.5	5.3	11.0	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	2.0	3.8	6.8	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	1.6	3.1	5.3	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.3	2.5	4.0	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.0	2.2	3.6	ns
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}</math>; <math>C_L = 10\text{ pF}</math></b>						
$t_{PHL}$ , $t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	21.0	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	2.4	6.1	13.0	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	2.4	4.4	7.9	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	2.0	3.7	6.2	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.4	3.0	4.7	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.3	2.8	4.3	ns
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}</math>; <math>C_L = 15\text{ pF}</math></b>						
$t_{PHL}$ , $t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	24.5	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	3.4	6.9	14.8	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	2.8	5.0	8.9	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	2.0	4.1	7.0	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.7	3.5	5.3	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.6	3.2	4.9	ns
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}</math>; <math>C_L = 30\text{ pF}</math></b>						
$t_{PHL}$ , $t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	34.8	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	4.6	9.2	20.1	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	3.0	6.5	11.8	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	2.6	5.4	9.3	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	2.4	4.6	7.1	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	2.3	4.3	6.5	ns

**Table 8. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
C <sub>PD</sub>	power dissipation capacitance	f = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>	[2]			
		V <sub>CC</sub> = 0.8 V	-	2.6	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.8	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	2.9	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.1	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	3.6	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	4.2	-	pF

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

**Table 9. Dynamic characteristics**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

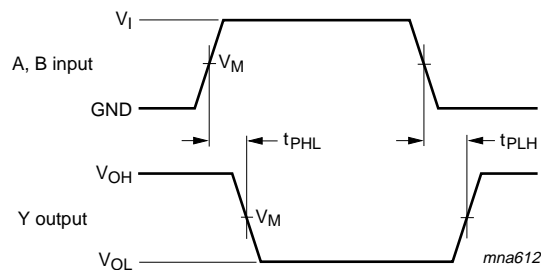
Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	
<b>C<sub>L</sub> = 5 pF</b>							
t <sub>PHL</sub> , t <sub>PLH</sub>	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.1	12.2	2.1	13.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	1.8	7.8	1.8	8.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.4	6.2	1.4	6.9	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.1	4.7	1.1	5.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	4.2	1.0	4.7	ns
<b>C<sub>L</sub> = 10 pF</b>							
t <sub>PHL</sub> , t <sub>PLH</sub>	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.2	14.4	2.2	15.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.2	9.2	2.2	10.2	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.9	7.3	1.9	8.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.3	5.6	1.3	6.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.2	4.9	1.2	5.4	ns



**Table 9. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	
<b><math>C_L = 15 \text{ pF}</math></b>							
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.1	16.5	3.1	18.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.5	10.5	2.5	11.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.0	8.3	2.0	9.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.5	6.4	1.5	7.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.4	5.7	1.4	6.3	ns
<b><math>C_L = 30 \text{ pF}</math></b>							
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	4.1	22.6	4.1	24.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.9	14.0	2.9	15.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.3	11.1	2.3	12.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.1	8.5	2.1	9.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.1	7.6	2.1	8.4	ns

## 12. Waveforms

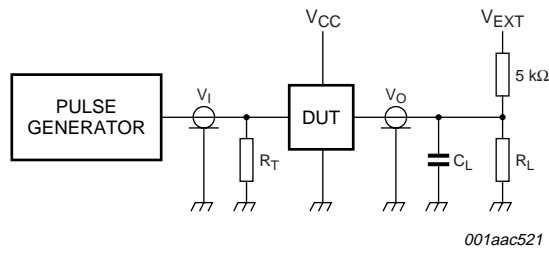


Measurement points are given in [Table 10](#).  
 Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage drop that occur with the output load.

**Fig 7. The data input (A or B) to output (Y) propagation delays**

**Table 10. Measurement points**

Supply voltage	Output	Input		
$V_{CC}$	$V_M$	$V_M$	$V_I$	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{CC}$	$\leq 3.0 \text{ ns}$



Test data is given in [Table 11](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 8. Load circuitry for switching times**

**Table 11. Test data**

Supply voltage	Load		$V_{EXT}$		
$V_{CC}$	$C_L$	$R_L$ [1]	$t_{PLH}, t_{PHL}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

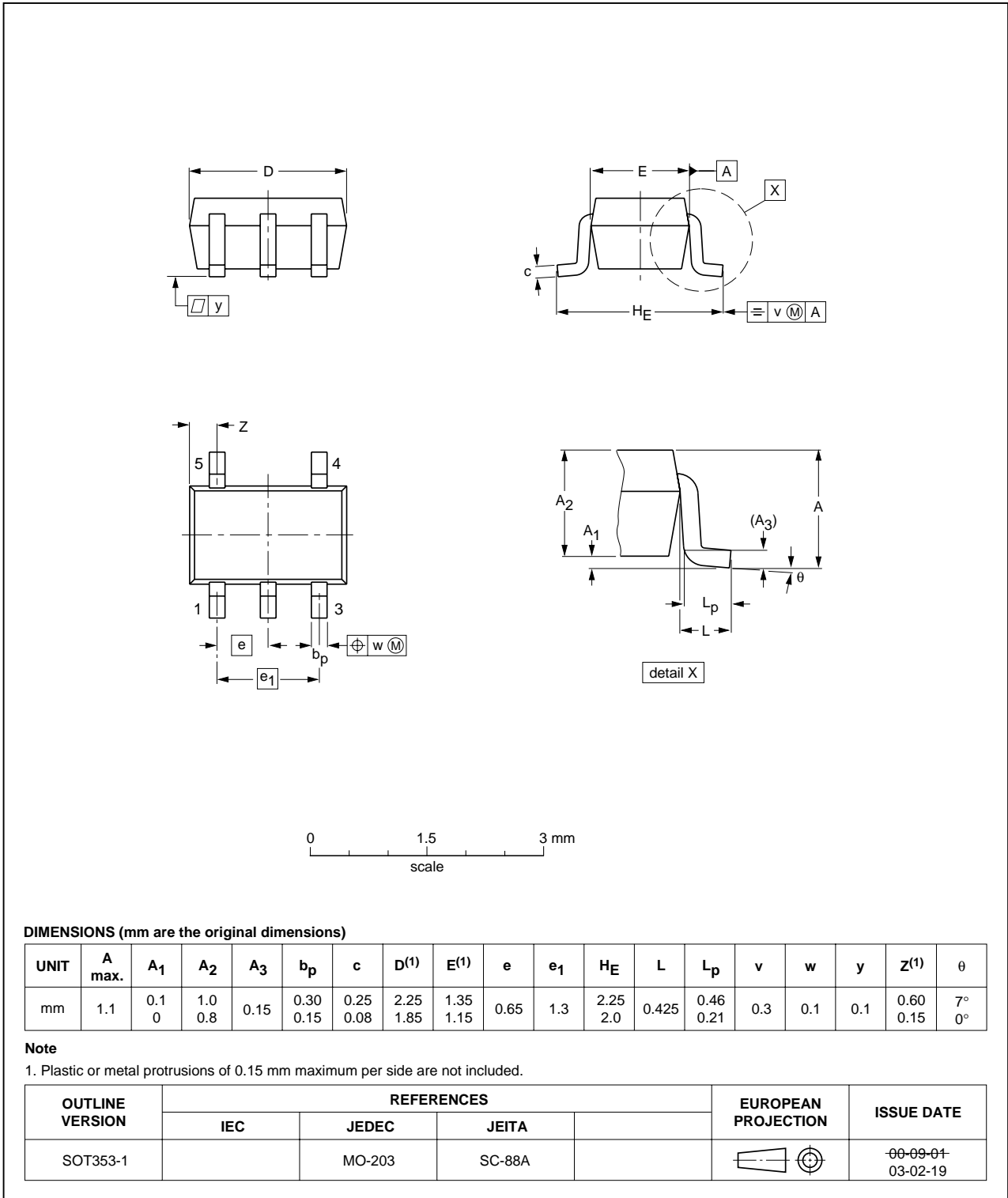


Fig 9. Package outline SOT353-1 (TSSOP5)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

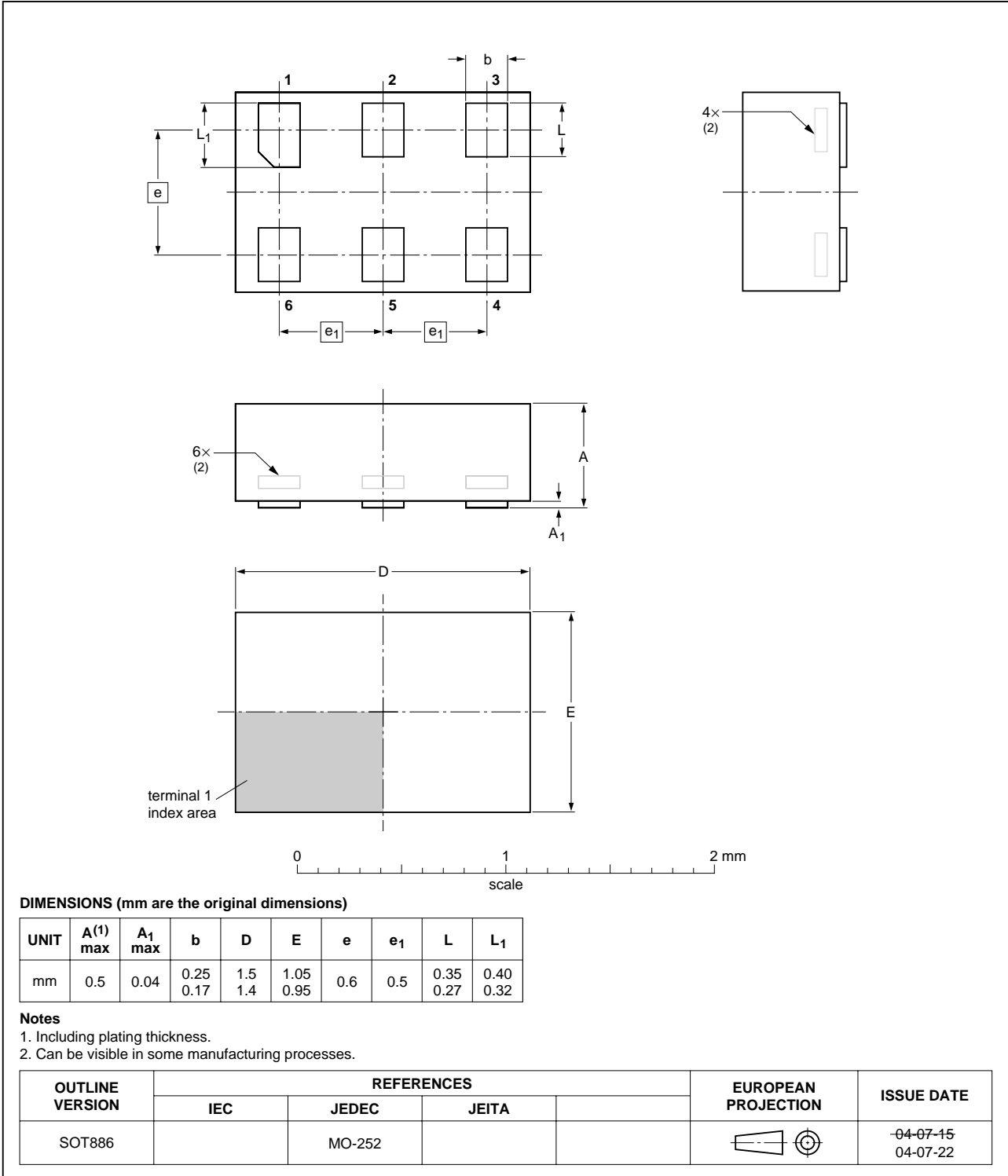


Fig 10. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

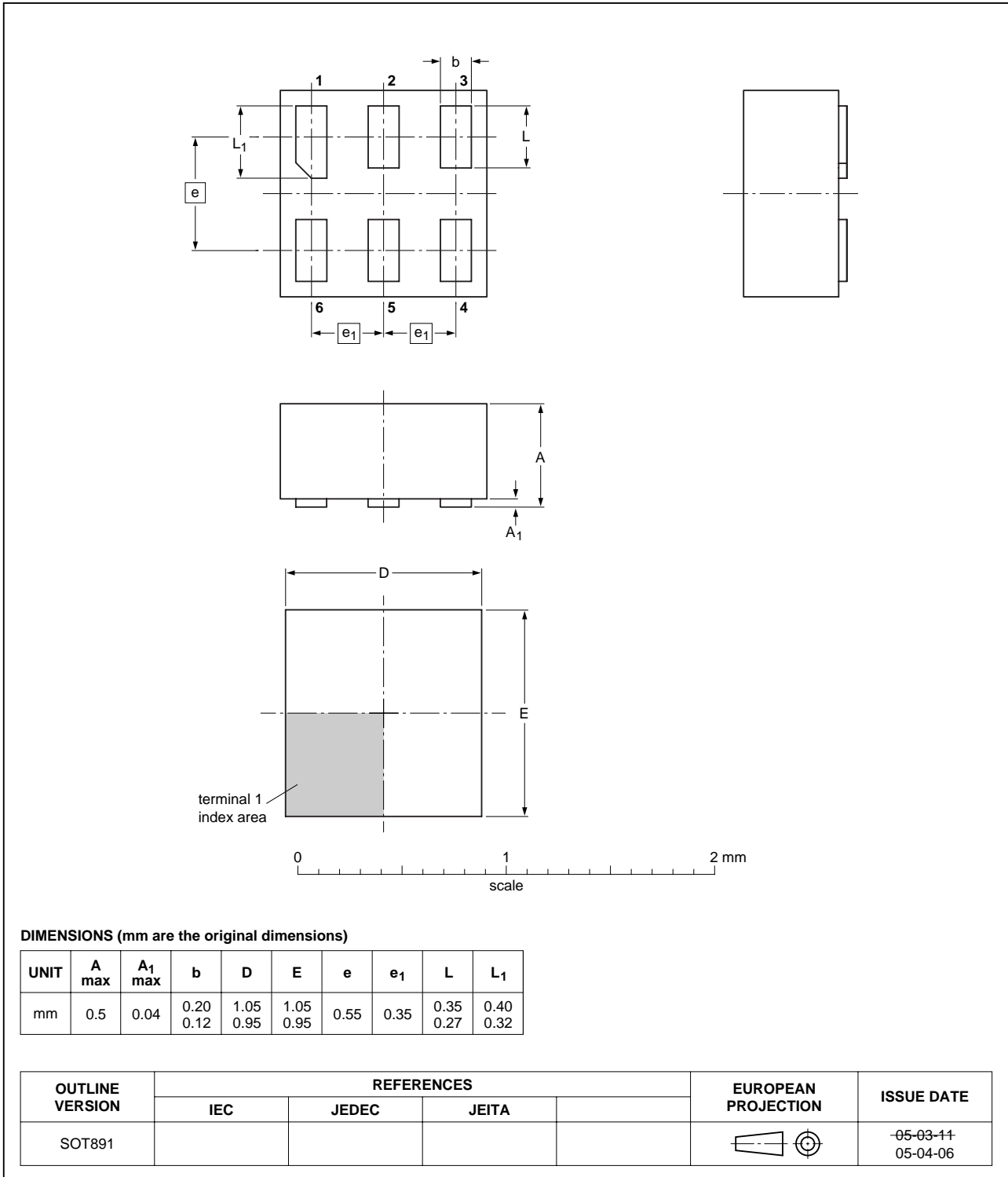


Fig 11. Package outline SOT891 (XSON6)

## 14. Abbreviations

Table 12: Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor Transistor Logic

## 15. Revision history

Table 13: Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G00_2	20060629	Product data sheet	-	74AUP1G00_1
Modifications:	<ul style="list-style-type: none"><li>• ESD HBM and <math>C_{PD}</math> values modified in <a href="#">Section 2</a>, <a href="#">Table 8</a></li><li>• Added type number 74AUP1G00GF (XSON6/SOT891) package</li></ul>			
74AUP1G00_1	20050711	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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